NSN 5961-01-055-7519

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view Online at https://aerobasegroup.com/nsn/5961-01-055-7519
Inclosure Material:
Metal
Overall Length:
1.252 inches
Overall Height:
0.340 inches
Overall Width:
0.700 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact-darlington connected
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
12.0 emitter to base voltage, dc and 80.0 collector to base voltage/static/emitter open and 80.0 collector to emitter reverse voltage
Current Rating Per Characteristic:
10.00 amperes source cutoff current and 0.50 amperes source cutoff current
Power Rating Per Characteristic:
25.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Precious Material And Location:
Terminal surface option gold
Precious Material:
Gold
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
3 uninsulated wire lead and 1 case
Specification Data:
81349-mil-s-19500/472 government specification
Shelf Life:
N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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